## NSN 5961-00-449-4230

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View Online at https://aerobasegroup.com/nsn/5961-00-449-4230 **Inclosure Material:** Metal **Overall Length:** 0.505 inches **Overall Diameter:** 0.650 inches **Mounting Facility Quantity: Internal Configuration:** Junction contact **Electrode Internally-electrically Connected To Case:** Anode **Mounting Method:** Threaded stud **Features Provided:** Hermetically sealed case **Overall Width Across Flats:** 0.562 inches **Thread Size:** 0.250 inches **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 720.0 breakover voltage, dc **Current Rating Per Characteristic:** 80.00 milliamperes forward current, total rms peak **Power Rating Per Characteristic:** 0.5 watts small-signal input power, common-collector outside diameter **Maximum Operating Tempurature Per Measurement Point:** 105.0 degrees celsius junction **Special Features:** Junction pattern arrangement: pnpn **Thread Series Designator:** Unf **Terminal Type And Quantity:** 1 threaded stud and 2 tab, solder lug Shelf Life: N/a **Unit Of Measure: Demilitarization:** 

No

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